



RELIABILITY REPORT  
FOR  
MAX19997AETX+  
PLASTIC ENCAPSULATED DEVICES

April 3, 2009

**MAXIM INTEGRATED PRODUCTS**

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## Conclusion

The MAX19997AETX+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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### I. Device Description

#### A. General

The MAX19997A dual downconversion mixer is a versatile, highly integrated diversity downconverter that provides high linearity and low noise figure for a multitude of 1800MHz to 2900MHz base-station applications. The MAX19997A fully supports both low- and high-side LO injection architectures for the 2300MHz to 2900MHz WiMAX(tm), LTE, WCS, and MMDS bands, providing 8.7dB gain, +24dBm input IP3, and 10.3dB NF in the low-side configuration, and 8.7dB gain, +24dBm input IP3, and 10.4dB NF in the high-side configuration. High-side LO injection architectures can be further extended down to 1800MHz with the addition of one tuning element (a shunt inductor) on each RF port. The device integrates baluns in the RF and LO ports, an LO buffer, two double-balanced mixers, and a pair of differential IF output amplifiers. The MAX19997A requires a typical LO drive of 0dBm and a supply current guaranteed below 420mA to achieve the targeted linearity performance. The MAX19997A is available in a compact 6mm x 6mm, 36-pin thin QFN lead-free package with an exposed pad. Electrical performance is guaranteed over the extended temperature range, from TC = -40°C to +85°C.

**II. Manufacturing Information**

A. Description/Function:	Dual, SiGe High-Linearity, High-Gain, 1800MHz to 2900MHz Downconversion Mixer with LO Buffer/Switch
B. Process:	G4
C. Number of Device Transistors:	
D. Fabrication Location:	Oregon
E. Assembly Location:	ASAT China, UTL Thailand
F. Date of Initial Production:	October 24, 2008

**III. Packaging Information**

A. Package Type:	36-pin TQFN 6x6
B. Lead Frame:	Copper
C. Lead Finish:	100% matte Tin
D. Die Attach:	Conductive Epoxy
E. Bondwire:	Gold (1 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#05-9000-2788
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	Level 1
J. Single Layer Theta Ja:	38°C/W
K. Single Layer Theta Jc:	1.4°C/W
L. Multi Layer Theta Ja:	28°C/W
M. Multi Layer Theta Jc:	1.4°C/W

**IV. Die Information**

A. Dimensions:	116 X 131 mils
B. Passivation:	Si <sub>3</sub> N <sub>4</sub>
C. Interconnect:	Au
D. Backside Metallization:	None
E. Minimum Metal Width:	1.2 microns (as drawn) Metal 1, 2 & 3 5.6 microns (as drawn) Metal 4
F. Minimum Metal Spacing:	1.6 microns (as drawn) Metal 1, 2 & 3, 4.2 microns (as drawn) Metal 4
G. Bondpad Dimensions:	5 mil. Sq.
H. Isolation Dielectric:	SiO <sub>2</sub>
I. Die Separation Method:	Wafer Saw

## V. Quality Assurance Information

- A. Quality Assurance Contacts: Ken Wendel (Director, Reliability Engineering)  
Bryan Preeshl (Managing Director of QA)
- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.  
0.1% For all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

## VI. Reliability Evaluation

### A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate ( $\lambda$ ) is calculated as follows:

$$\lambda = \frac{1}{\text{limit) MTTF}} = \frac{1.83}{192 \times 4340 \times 48 \times 2} \quad (\text{Chi square value for MTTF upper})$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 22.4 \times 10^{-9}$$

$\lambda = 22.4$  F.I.T. (60% confidence level @ 25°C)

This low failure rate represents data collected from Maxim's reliability monitor program. In addition to routine production Burn-In, Maxim pulls a sample from every fabrication process three times per week and subjects it to an extended Burn-In prior to shipment to ensure its reliability. The reliability control level for each lot to be shipped as standard product is 59 F.I.T. at a 60% confidence level, which equates to 3 failures in an 80 piece sample. Maxim performs failure analysis on any lot that exceeds this reliability control level. Attached Burn-In Schematic (Spec. # ) shows the static Burn-In circuit. Maxim also performs quarterly 1000 hour life test monitors. This data is published in the Product Reliability Report (RR-1N). Current monitor data for the S4 Process results in a FIT Rate of @ 25C and @ 55C (0.8 eV, 60% UCL)

### B. Moisture Resistance Tests

The industry standard 85°C/85%RH or HAST testing is monitored per device process once a quarter.

### C. E.S.D. and Latch-Up Testing

The CR41-1 die type has been found to have all pins able to withstand a HBM transient pulse of +/-1500 V per JEDEC JESD22-A114. Latch-Up testing has shown that this device withstands a current of +/-250 mA, 1.5x VCCMax Overvoltage per JESD78.

**Table 1**  
Reliability Evaluation Test Results

**MAX19997AETX+**

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES
<b>Static Life Test</b> (Note 1)	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality	48	0
<b>Moisture Testing</b> (Note 2) 85/85	Ta = 85°C RH = 85% Biased Time = 1000hrs.	DC Parameters & functionality	77	0
<b>Mechanical Stress</b> (Note 2) Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters & functionality	77	0

Note 1: Life Test Data may represent plastic DIP qualification lots. Note 2: Generic Package/Process data